

Supplementary materials

Reset first resistive switching in Ni_{1-x}O thin films as charge transfer insulator deposited by reactive RF magnetron sputtering

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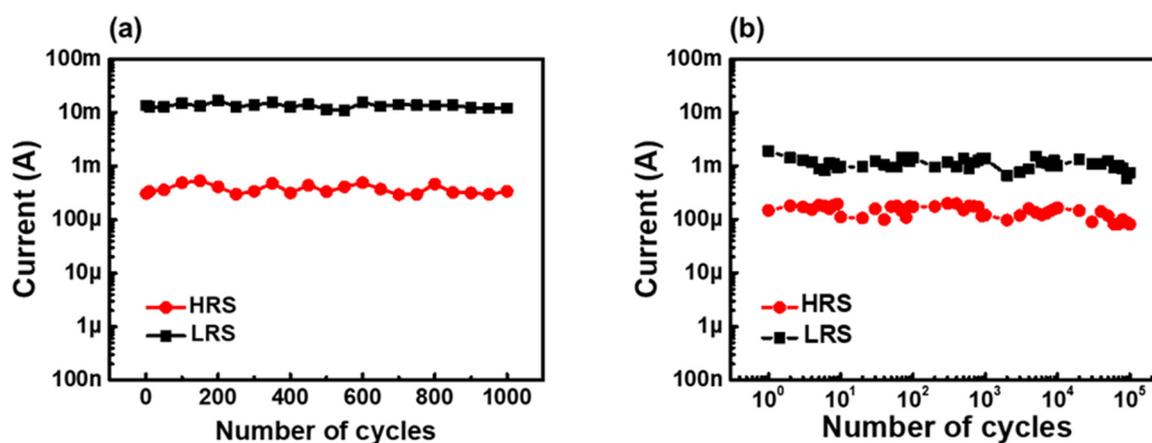


Figure S1. Endurance characteristics of Ni_{1-x}O bipolar RS device with (a) DC cycles measured with V_{read} of ± 0.25 V, and (b) AC pulses cycles measured with a set pulse (V_{set}) of -0.95 V with 180 ns, a reset pulse (V_{reset}) of 1.2 V with 180 ns and V_{read} of 0.3 V.